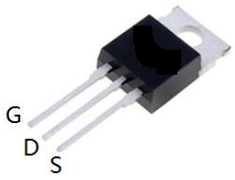
-30V/-100A P-Channel Advanced Power MOSFET **VS3506AT**

Features

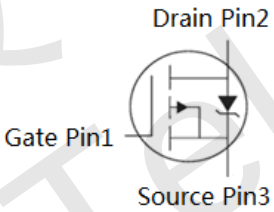
- P-Channel，-5V Logic Level Control
- Enhancement mode
- Low on-resistance RDS(on) @ V_{GS}=-4.5 V
- Fast Switching and High efficiency
- 100% Avalanche Tested
- Pb-free lead plating; RoHS compliant

V_{DS}	-30	V
$R_{DS(on),TYP}$@ V_{GS}=-10 V	6.2	mΩ
$R_{DS(on),TYP}$@ V_{GS}=-4.5V	10	mΩ
I_D	-100	A

TO-220AB



Pb-Free RoHS



Part ID	Package Type	Marking	Tape and reel information
VS3506AT	TO-220AB	3506AT	50pcs/Tube

Maximum ratings, at T_A =25 °C, unless otherwise specified

Symbol	Parameter		Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage		-30	V
VGS	Gate-Source voltage		±20	V
I_S	Diode continuous forward current	T_C =25°C	-100	A
I_D	Continuous drain current @V_{GS}=-10V	T_C =25°C	-100	A
		T_C =100°C	-71	A
I_{DM}	Pulse drain current tested ①	T_C =25°C	-400	A
I_{DSM}	Continuous drain current @VGS=-10V	T_A=25°C	-15	A
		T_A=70°C	-12	A
EAS	Avalanche energy, single pulsed ②		163	mJ
P_D	Maximum power dissipation	T_C =25°C	94	W
P_{DSM}	Maximum power dissipation ③	T_A=25°C	2	W
T_{STG} , T_J	Storage and Junction Temperature Range		-55 to 175	°C
Thermal Characteristics				
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		1.6	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		62.5	°C/W

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-30V/-100A P-Channel Advanced Power MOSFET **VS3506AT**

Typical Characteristics

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=-250μA	-30	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-30V,V_{GS}=0V	--	--	-1	μA
	Zero Gate Voltage Drain Current(Tj=125℃)	V_{DS}=-30V,V_{GS}=0V	--	--	-100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V,V_{DS}=0V	--	--	±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=-250μA	-1.2	--	-2.3	V
$R_{DS(ON)}$	Drain-Source On-State Resistance ④	V_{GS}=-10V, I_D=-30A	--	6.2	8.7	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance ④	V_{GS}=-4.5V, I_D=-20A	--	10	14	mΩ
Dynamic Electrical Characteristics @ T_J= 25°C (unless otherwise stated)						
C_{iss}	Input Capacitance	V_{DS}=-15V,V_{GS}=0V, f=1MHz	3765	4430	5090	pF
C_{oss}	Output Capacitance		445	525	600	pF
C_{rss}	Reverse Transfer Capacitance		365	430	490	pF
R_g	Gate Resistance	f=1MHz	--	4.6	--	Ω
Q_g (10V)	Total Gate Charge	V_{DS}=-15V,I_D=-30A, V_{GS}=-10V	--	73	--	nC
Q_g (4.5V)	Total Gate Charge		--	41	--	nC
Q_{gs}	Gate-Source Charge		--	12	--	nC
Q_{gd}	Gate-Drain Charge		--	18	--	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=-15V, I_D=-30A, R_G=3.0Ω, V_{GS}=-10V	--	12	--	ns
t_r	Turn-on Rise Time		--	8.5	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	77.5	--	ns
t_f	Turn-Off Fall Time		--	19.5	--	ns
Source- Drain Diode Characteristics@ T_J= 25°C (unless otherwise stated)						
V_{SD}	Forward on voltage	I_{SD}=-30A,V_{GS}=0V	--	-0.9	-1.2	V
t_{rr}	Reverse Recovery Time	T_j=25℃,I_{sd}=-30A, V_{GS}=0V di/dt=-500A/μs	--	31	--	ns
Q_{rr}	Reverse Recovery Charge		--	15.5	--	nC

NOTE:

① Repetitive rating; pulse width limited by max junction temperature.

② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.5mH,R_G = 25Ω, I_{AS} = -20A, V_{GS} =-10V. Part not recommended for use above this value

③ The power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C.

④ Pulse width ≤ 300μs; duty cycle≤ 2%.

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Typical Characteristics

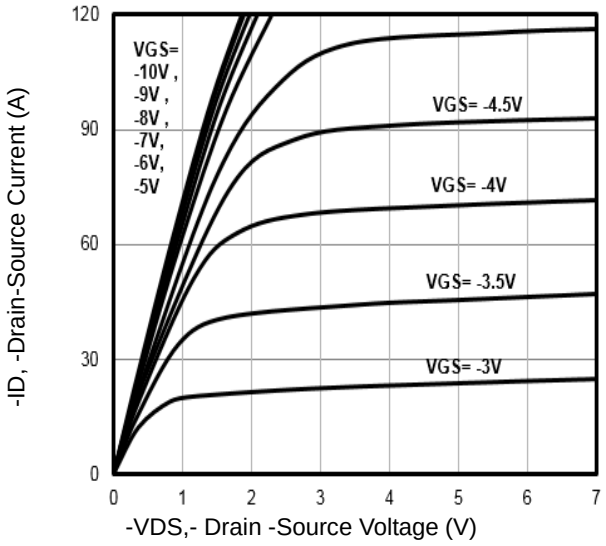

Fig1. Typical Output Characteristics

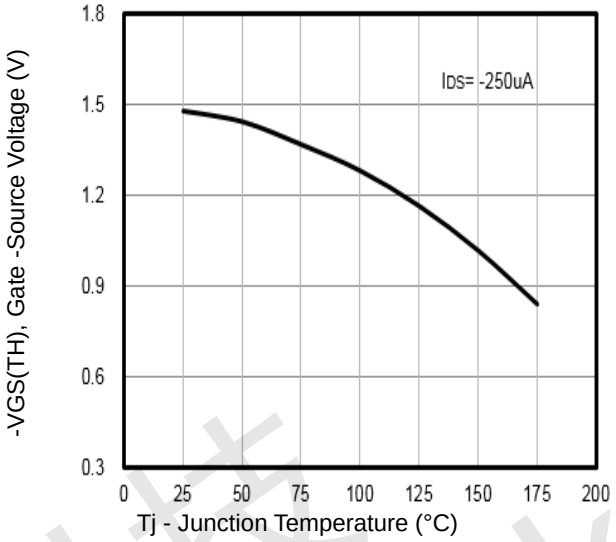

Fig2. $-V_{GS(TH)}$ Gate -Source Voltage Vs.Tj

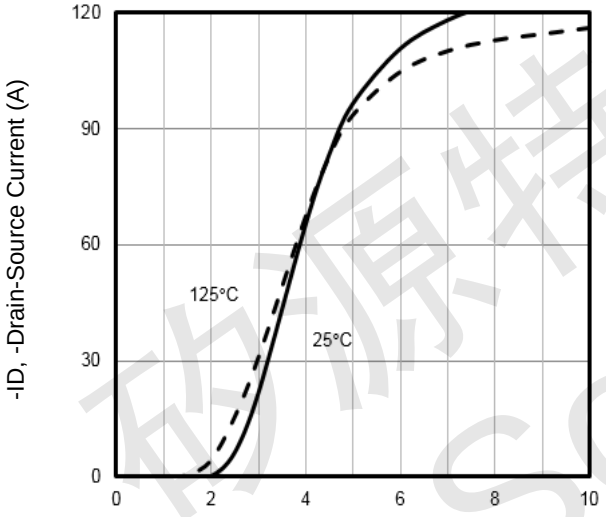

Fig3. Typical Transfer Characteristics

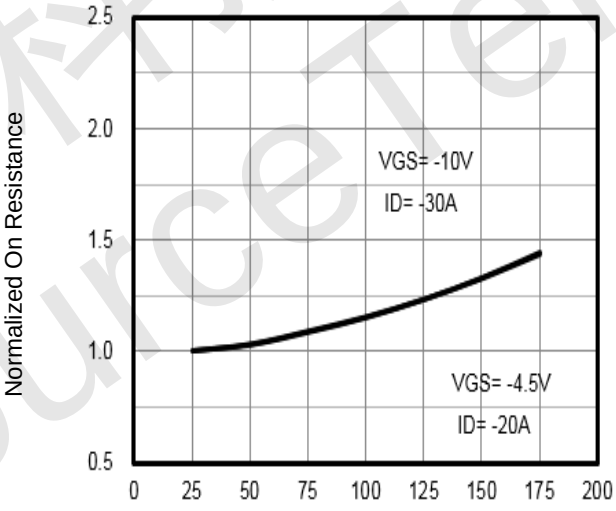

Fig4. Normalized On-Resistance Vs. Tj

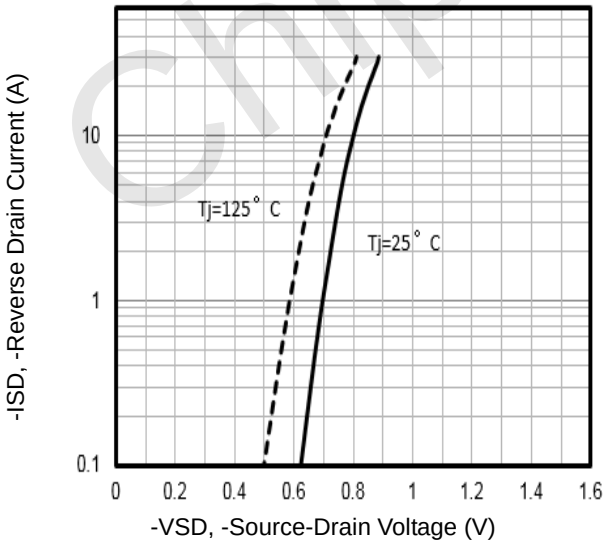

Fig5. Typical Source-Drain Diode Forward Voltage

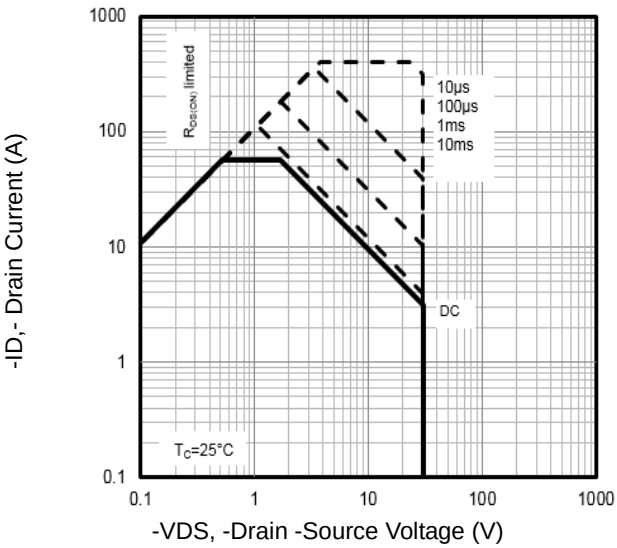

Fig6. Maximum Safe Operating Area

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Typical Characteristics

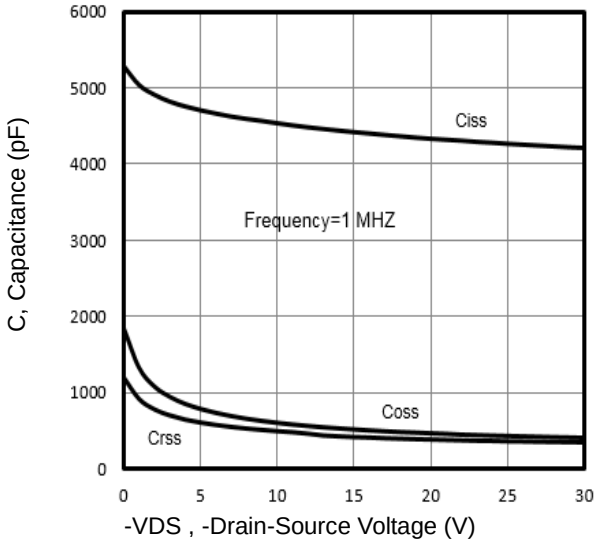

Fig7. Typical Capacitance Vs.Drain-Source Voltage

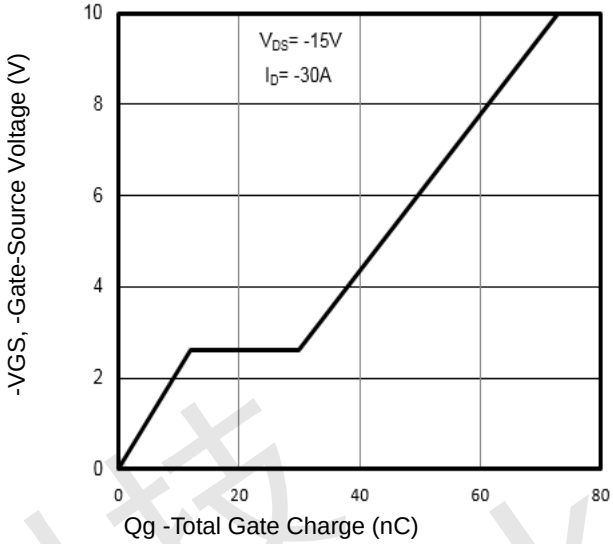

Fig8. Typical Gate Charge Vs.Gate-Source Voltage

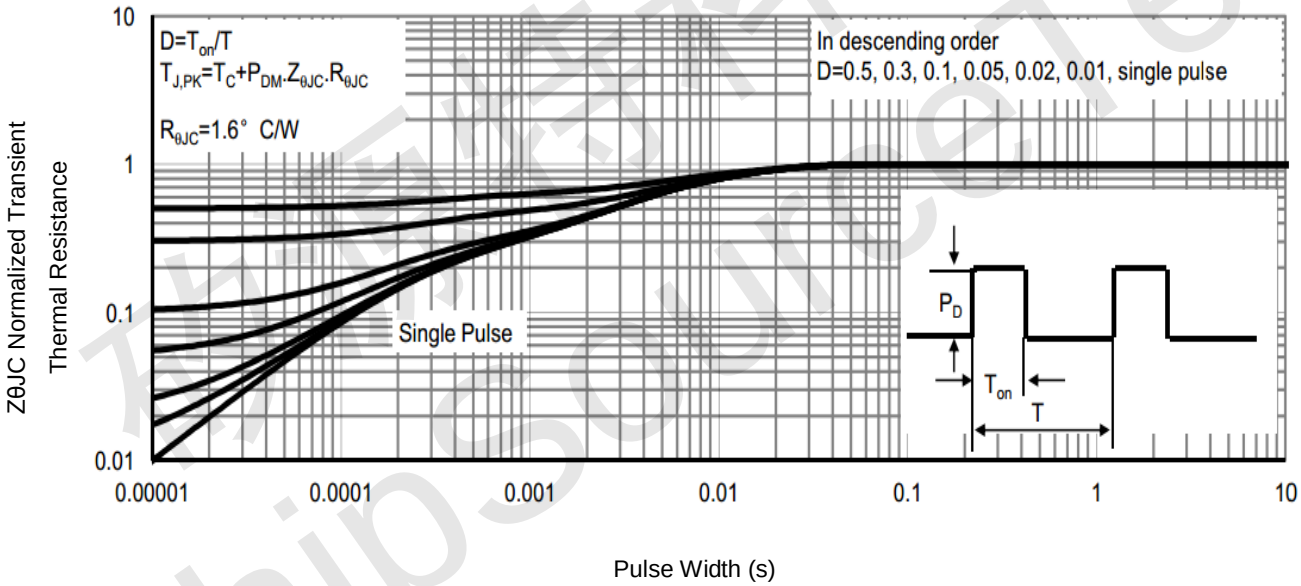

Fig9. Normalized Maximum Transient Thermal Impedance

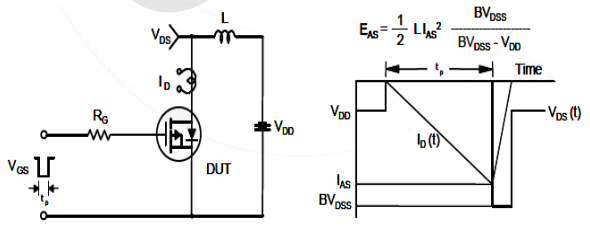

Fig10. Unclamped Inductive Test Circuit and Waveforms

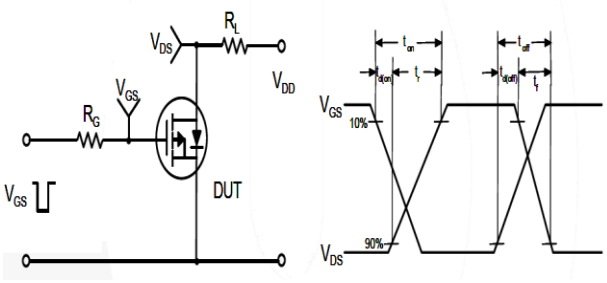

Fig11. Switching Time Test Circuit and waveforms

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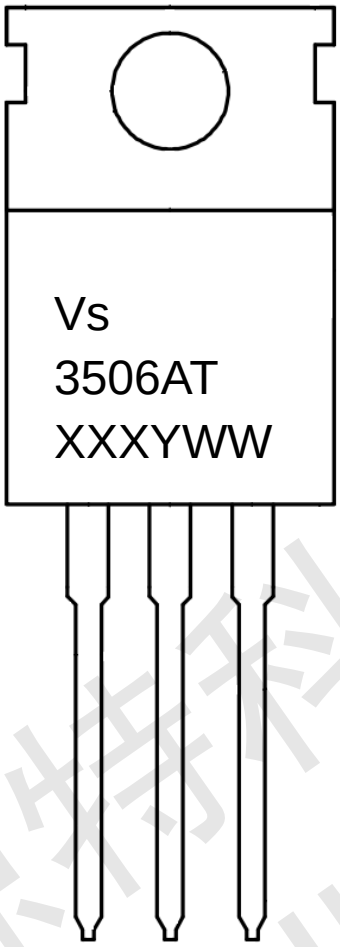
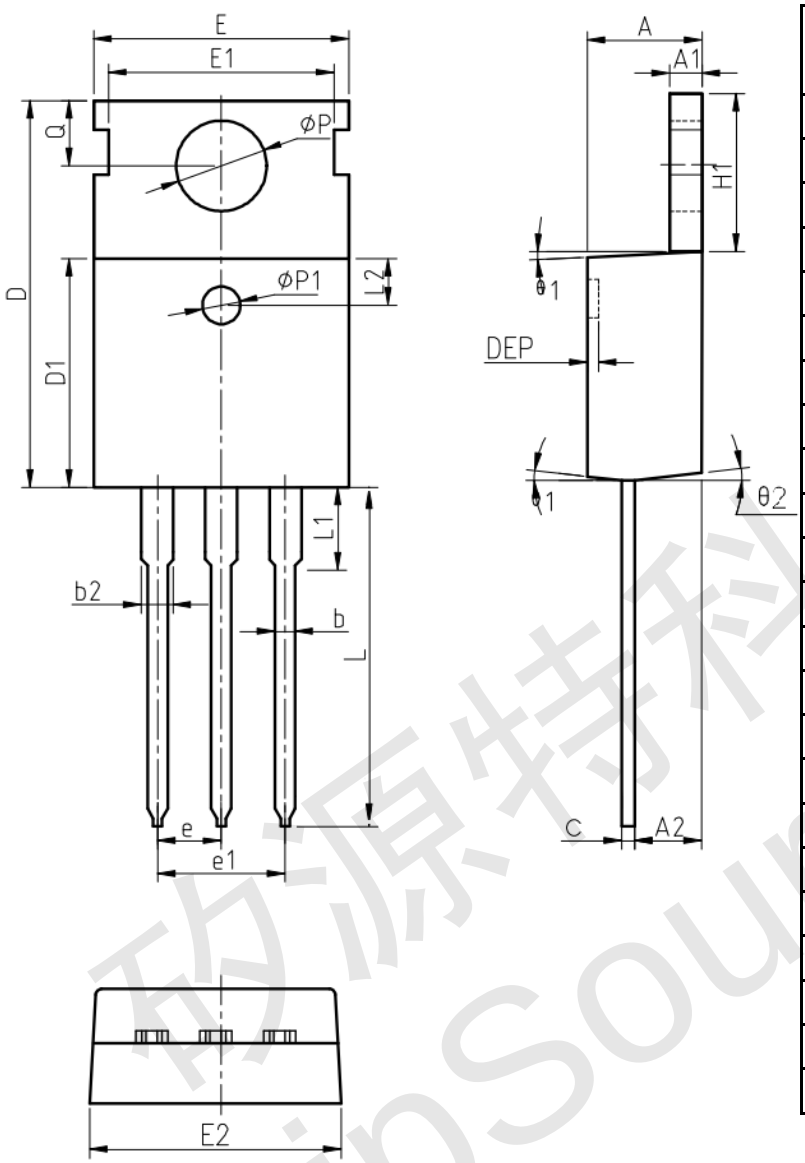
Marking Information



1st line： Vanguard Code（Vs）
2nd line： Part Number（3506AT）
3rd line： Date code （XXXYWW）
XXX： Wafer Lot Number
Y： Year Code， e.g. E means 2017
WW： Week Code

TO-220AB Package Outline Data



Symbol	Dimensions (unit: mm)		
	Min	Typ	Max
A	4.30	4.52	4.70
A1	1.15	1.30	1.40
A2	2.20	2.40	2.60
b	0.70	0.80	1.00
b2	1.17	1.32	1.50
c	0.45	0.50	0.61
D	15.30	15.65	15.90
D1	9.00	9.20	9.40
DEP	0.05	0.10	0.25
E	9.66	9.90	10.28
E1	-	8.70	-
E2	9.80	10.00	10.20
ΦP1	1.40	1.50	1.60
e	2.54 BSC		
e1	5.08 BSC		
H1	6.40	6.50	6.80
L	12.70	-	14.27
L1	-	-	3.95
L2	2.40	2.50	2.60
ΦP	3.53	3.60	3.70
Q	2.70	2.80	2.90
θ1	5 °	7 °	9 °
θ2	1 °	3 °	5 °

Notes:

1. Refer to JEDEC TO-220 variation AB
2. Dimension "D" and "E" do NOT include mold flash. Mold flash shall not exceed 0.127mm per side.

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